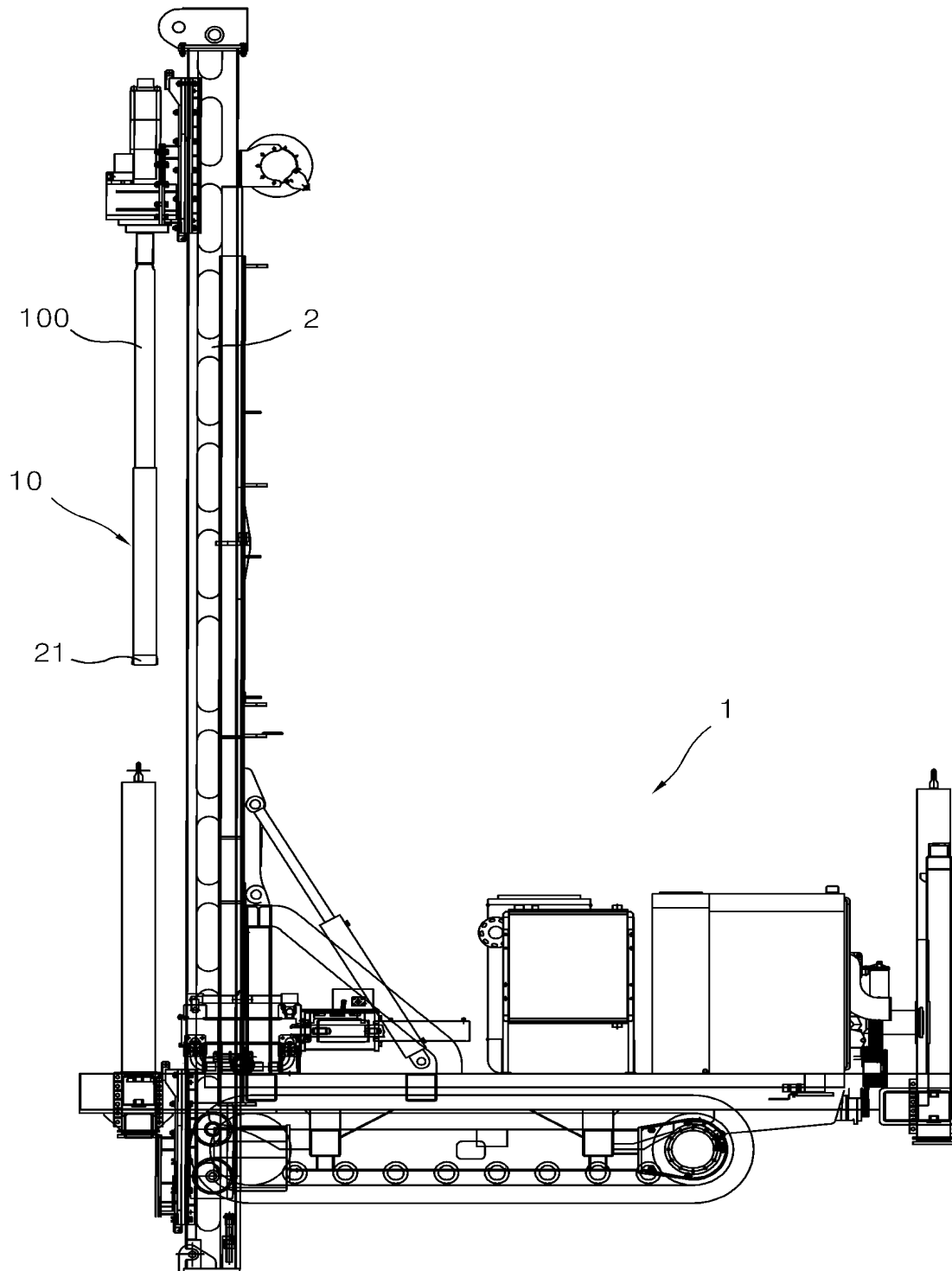
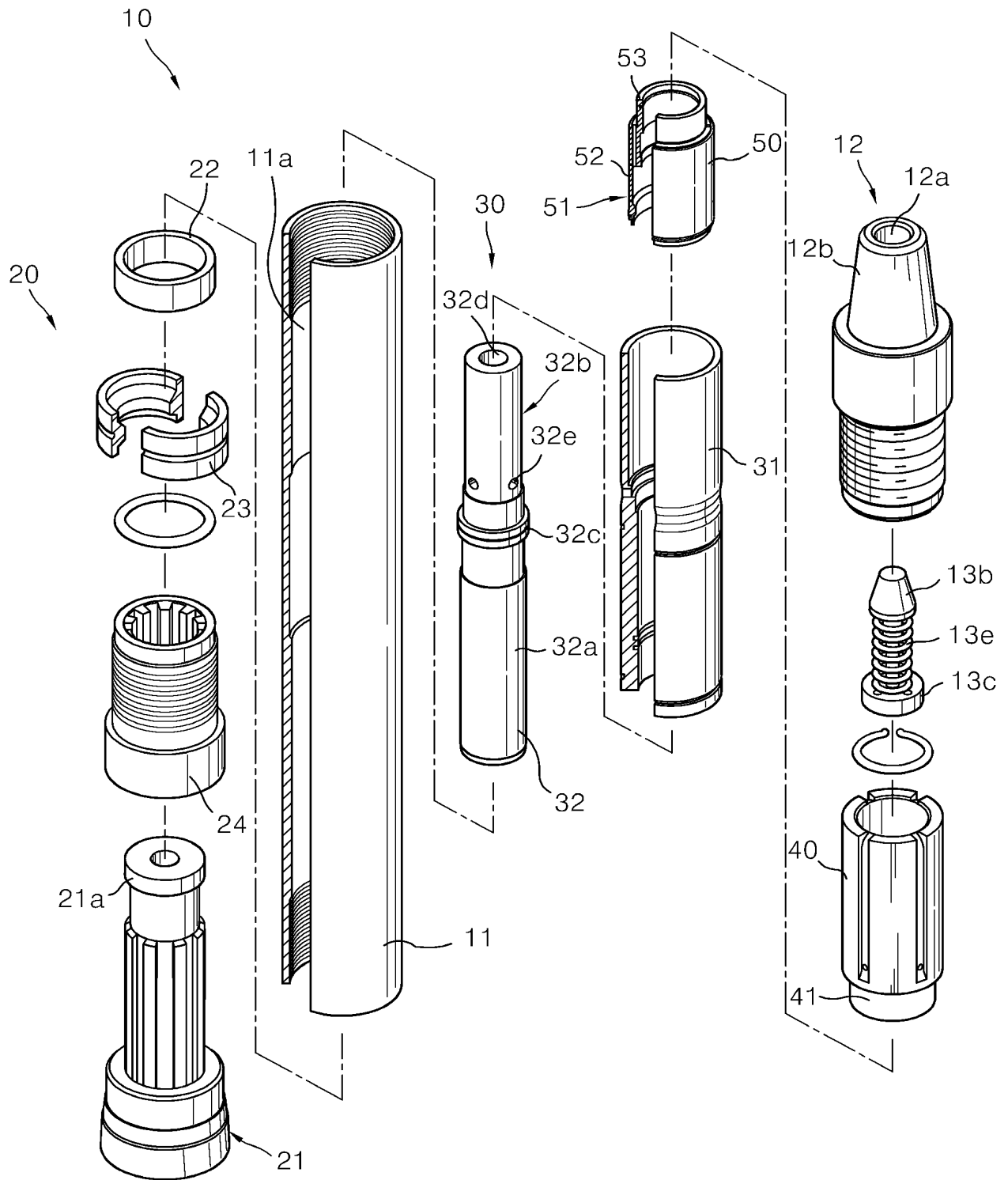


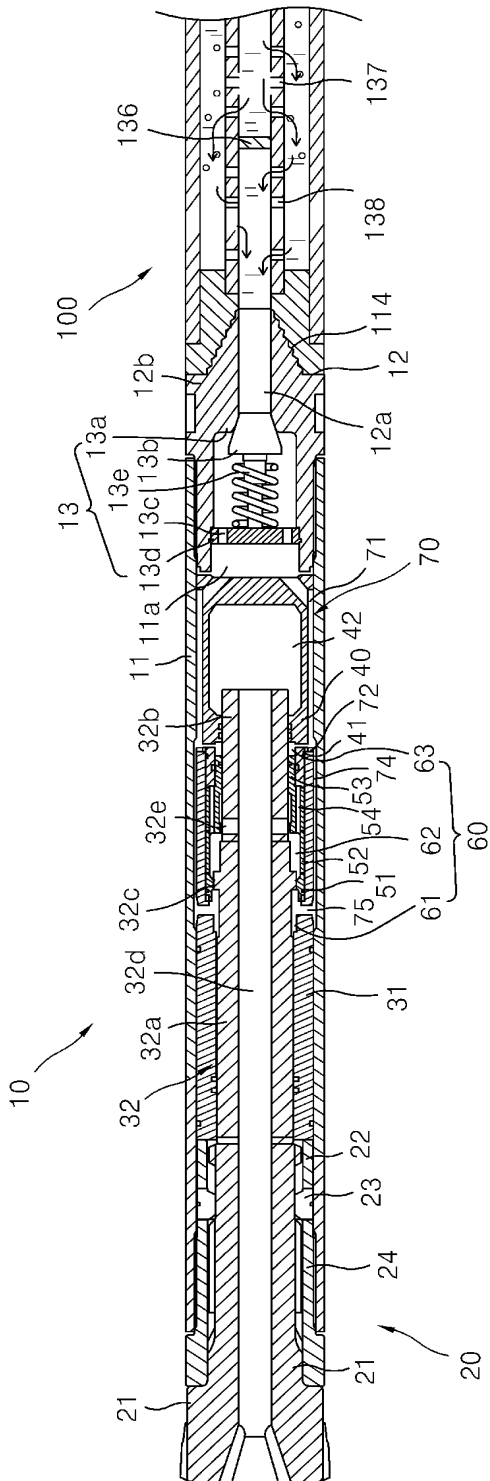
[Fig. 1]



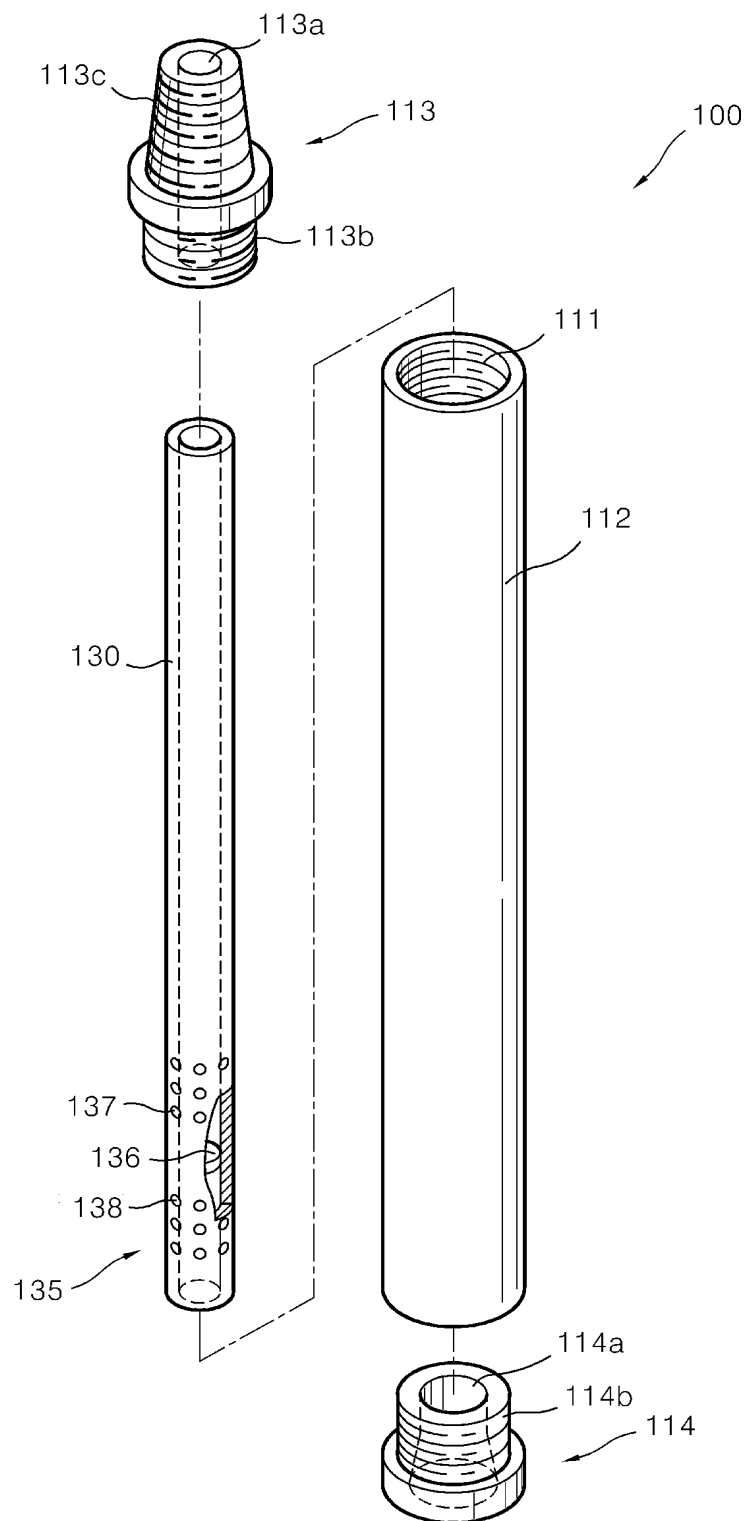
[Fig. 2]



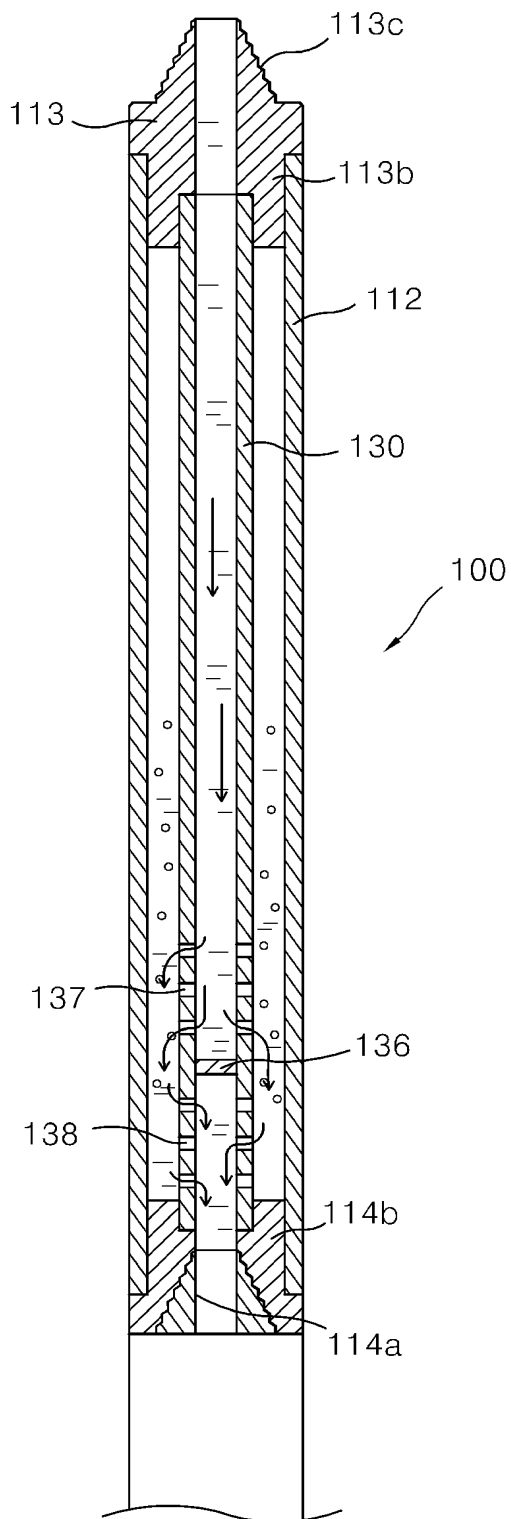
[Fig. 3]



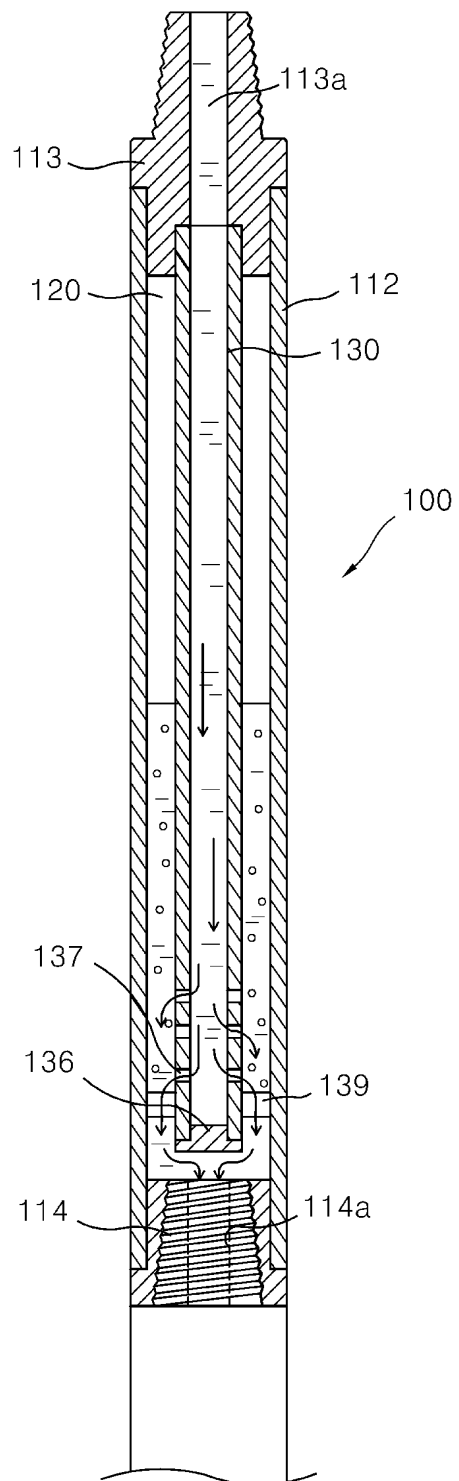
[Fig. 4]



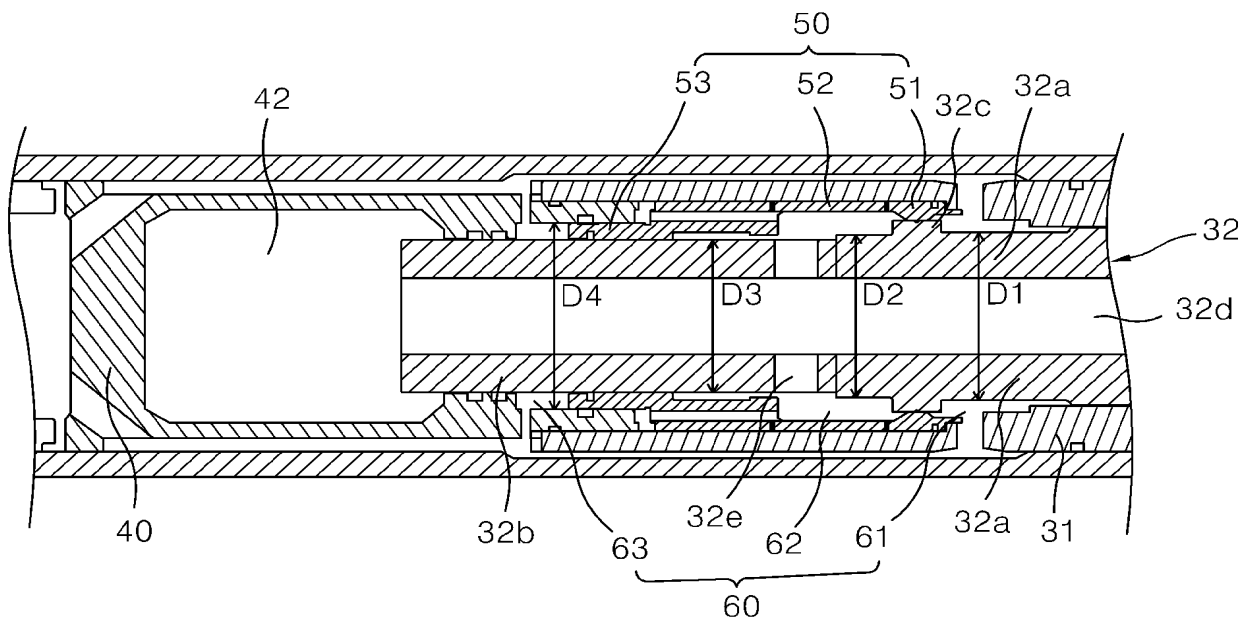
[Fig. 5]



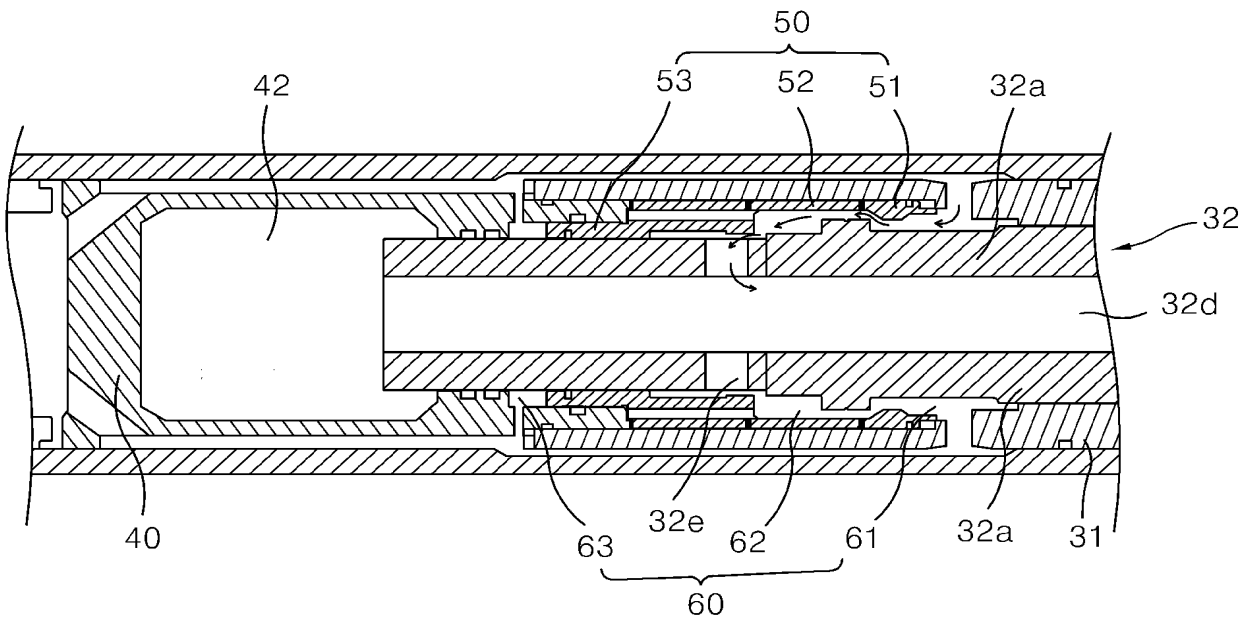
[Fig. 6]



[Fig. 7]



[Fig. 8]



[illegible]

A detailed cross-sectional diagram of a semiconductor device. The device consists of several stacked layers. At the top is a thin layer labeled 71. Below it is a thicker layer containing various components: 72, 53, 50, 74, 54, 52, 75, 51, 61, 75, 11, and 31. Arrows indicate fluid flow or electrical paths through these layers. A central horizontal channel or cavity is formed by layers 50, 54, and 52. Below this is another layer containing components 63, 32c, 32e, and 62. The bottom-most layer is labeled 32, with a sub-layer 32d indicated below it. The entire structure is bounded by vertical lines on the left and right.



[Fig. 12]

